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RCE/1700

NOV 13 2002

Honeywell's Docket No. 30-4790 (4780)
Practitioner's Docket No. 100595.0048US3

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Zhang, et al.

Application No.: 09/357,264

Group No.: 1765

Filed: July 19, 1999

Examiner: Charlotte A. Brown

For: Composition for Chemical Mechanical Planarization of Copper, Tantalum and Tantalum Nitride

Box RCE
Assistant Commissioner for Patents
Washington, D.C. 20231

REQUEST FOR CONTINUED EXAMINATION (RCE)
(37 C.F.R. 1.114)

1. Applicant hereby requests continued examination, in accordance with 37 C.F.R. Section 1.114, for the above identified application.

CERTIFICATION UNDER 37 C.F.R. SECTIONS 1.8(a) AND 1.10
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(Request for Continued Examination (RCE))--page 1 of 3)



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WASHINGTON, D.C. 20231

Inventor: **Zhang et al.**

Serial No: **09/357264**

Filed: **July 19, 1999**

For: **Comp. for Chemical Mechanical
Planarization of Copper,
Tantalum and Tantalum Nitride**

Examiner: Brown, Charlotte A.

Art Unit: **1765**

PRELIMINARY AMENDMENT

The Honorable Commissioner
of Patents and Trademarks
Washington, D.C. 20231

Dear Sir:

IN THE CLAIMS

19. A method of accomplishing chemical mechanical planarization of a Cu/Ta/TaN surface comprising:

providing a single-step slurry solution including a combination selected from the group consisting of (i) H₂O₂ with H₃PO₄, H₂SO₄, HNO₃, oxalic acid, acetic acid, or organic acid, (ii) HNO₃ with H₃PO₄, or H₂SO₄; and (iii) an oxidizing reagent with HF;

applying the solution to the surface; and

planarizing both the Cu and at least one of the Ta and TaN during a single processing step.

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